

PIN Photodiode

25 Gbps
850 nm



**> GaAs PIN
Photodiode**

**> High speed up to
25 Gbps**

> 4 inch wafer

> Low bias voltage

> Low dark current

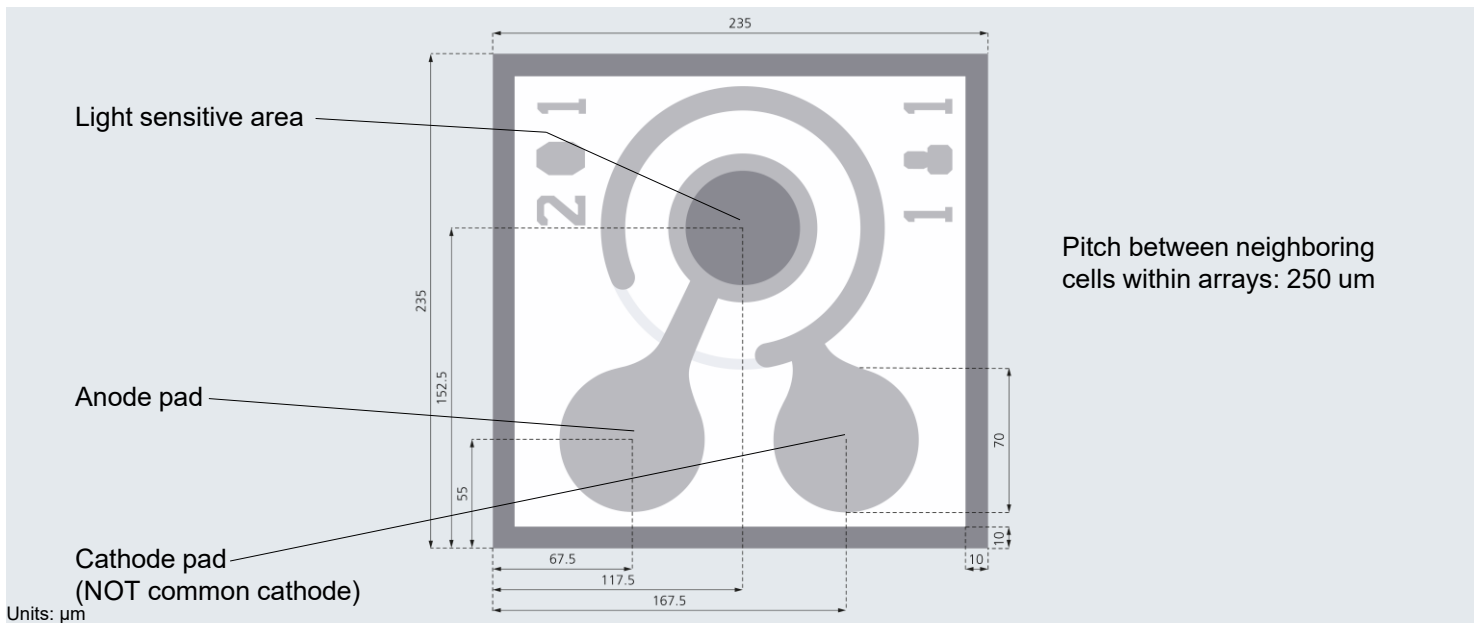
**> Available in
1x1, 1x4, 1x12**

Datasheet: 25 Gbps 850 nm Photodiode

Electro-Optical Characteristics ($U_{\text{bias}} = -2 \text{ V}$, $T = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Units	Notes
Wavelength range	λ	840	850	860	nm	
Substrate temperature	T_s	0	-	90	$^\circ\text{C}$	
Active area diameter	d_{act}	38	42	47	μm	
Small signal bandwidth	f_{6dB}	16	20	-	GHz	50 Ω load
Responsivity	R	0.5	0.6	0.7	A/W	
Dark current	I_{d1}	-	0.02	1	nA	
Capacitance	C	120	140	160	fF	50 Ω load

Dimensions



Product variants

Type	Single chip	1 x 4 line array	1 x 12 line array
Part number	TPD-25(01)-850-A0	TPD-25(04)-850-A0	TPD-25(12)-850-A0
Ordering number	ULMPIN-25-TT-N0101U (PD11)	ULMPIN-25-TT-N0104U (PD11)	ULMPIN-25-TT-N0112U (PD11)
Dimensions	235 x 235 x 150 μm	235 x 985 x 150 μm	235 x 2985 x 150 μm
Wiring		Electrically separated channels	Electrically separated channels

For more information visit
www.trumpf.com/s/VCSEL-solutions

Safety information:



Electrostatic sensitive devices / observe precautions for handling

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